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Filing Date	May 8, 2001	
First Named Inventor	Ejaz UI Haq	
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Examiner Name	Unassigned DINI+ UC	
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Examiner Initials * Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. "IEEE Standard for Low-Voltage Differential Signals (LVDS) for Scalable Coherent Interface (SCI)*, IEEE Std. 1596.3-1996, March 21, 1996, XP-002106653, Introduction, Contents and pages 1-30. 4M x 18 SLDRAM Preliminary Data Sheet 9/97 from SLDRAM Consortium. 1M x 16Bit x 4 BANKS DDR SDRAM (Rev. 0.5 June 1997) from Samsung. Kim, et al. "A 640MB/s Bi-Directional Data Strobed, Double-Data-Rate SDRAM with a 40mW DLL Circuit for a 256MB Memory System", ISSCC98 Digest, pp. 158-159, February 6, 1998.
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